



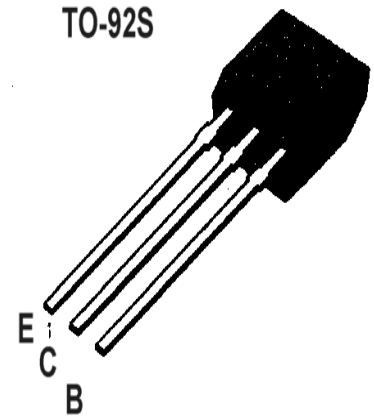
《风光欣》技术资料

2SC4115S

NPN EPITAXIAL SILICON TRANSISTOR

ABSOLUTE MAXIMUM RATINGS(TA=25)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	20	V
Emitter -Base Voltage	V _{EBO}	6	V
Collector Current	I _c	3	A
Collector Dissipation	P _c	0.3	W
Junction Temperature	T _J	150	
Storage Temperature	T _{STG}	-55 ~ +150	



ELECTRICAL CHARACTERISTICS(TA=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV _{CBO}	I _C = 50 μ A, I _E =0	40			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C = 1mA, I _B =0	20			V
Emitter -Base Breakdown Voltage	BV _{EBO}	I _E = 50 μ A, I _C =0	6			V
Collector Cut-off Current	I _{CBO}	V _{CB} = 30V, I _E =0			100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 5V, I _C =0,			100	nA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 2A, I _B =0.1A		0.2	0.5	V
DC Current Gain	h _{FE}	V _{CE} = 2V, I _C =100mA,	120		560	
Transition frequency	f _T	V _{CE} = 2V, I _C = -500mA		290		MHZ
Output Capacitance	C _{OB}	V _{CB} = 10V, I _E = 0, f=1MHZ		25		pF

h_{FE} CLASSIFICATION

Ltem	Q	R	S
H _{FE}	120-270	180-390	270-560